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FSAM20SH60A Motion SPM[®] 2 Series

Features

- UL Certified No. E209204 (UL1557)
- 600 V 20 A 3-Phase IGBT Inverter with Integral Gate Drivers and Protection
- · Low-Loss, Short-Circuit Rated IGBTs
- Low Thermal Resistance Using Ceramic Substrate
- Separate Open-Emitter Pins from Low Side IGBTs for Three-Phase Current Sensing
- Single-Grounded Power Supply
- Optimized for 15 kHz Switching Frequency
- Built-in NTC Thermistor for Temperature Monitoring
- Inverter Power Rating of 1.5 kW / 100~253 VAC
- Adjustable Current Protection Level via Selection of Sense-IGBT Emitter's External Rs
- Isolation Rating: 2500 V_{rms} / min.

Applications

Motion Control - Home Appliance / Industrial Motor

Resource

• AN-9043 - Motion SPM® 2 Series User's Guide

January 2014

General Description

FSAM20SH60A is a Motion SPM® 2 module providing a fully-featured, high-performance inverter stage for AC Induction, BLDC, and PMSM motors. These modules integrate optimized gate drive of the built-in IGBTs to minimize EMI and losses, while providing multiple on-module protection also features including under-voltage lockouts, overcurrent shutdown, thermal monitoring, and fault reporting. The built-in, high-speed HVIC requires only a single supply voltage and translates the incoming logic-level gate inputs to the high-voltage, high-current drive signals required to properly drive the module's internal IGBTs. Separate negative IGBT terminals are available for each phase to support the widest variety of control algorithms.

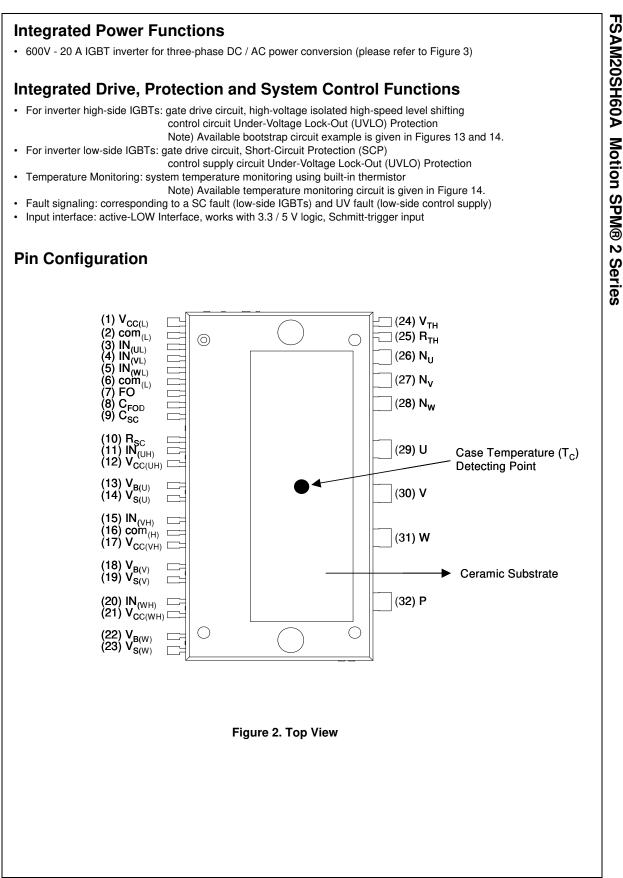


Figure 1. Package Overview

Package Marking and Ordering Information

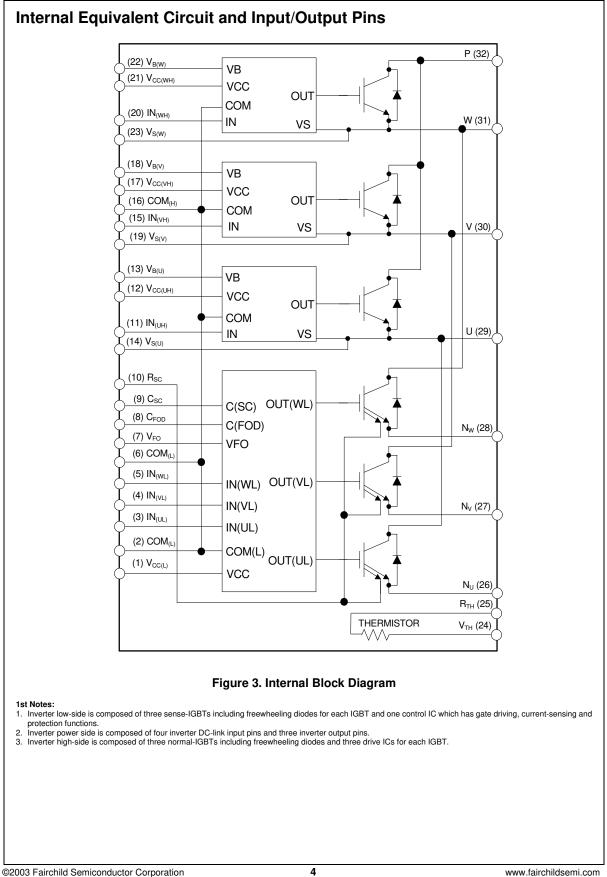
Device	Device Marking	Package	Packing Type	Quantity
FSAM20SH60A	FSAM20SH60A	S32AA-032	Rail	8

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n Number	Pin Name	Pin Description
1	V _{CC(L)}	Low-Side Common Bias Voltage for IC and IGBTs Driving
2	COM _(L)	Low-Side Common Supply Ground
3	IN _(UL)	Signal Input Terminal for Low-Side U-Phase
4	IN _(VL)	Signal Input Terminal for Low-Side V-Phase
5	IN _(WL)	Signal Input Terminal for Low-Side W-Phase
6	COM _(L)	Low-Side Common Supply Ground
7	V _{FO}	Fault Output
8	C _{FOD}	Capacitor for Fault Output Duration Selection
9	C _{SC}	Capacitor (Low-Pass Filter) for Short-Circuit Current Detection Input
10	R _{SC}	Resistor for Short-Circuit Current Detection
11	IN _(UH)	Signal Input for High-Side U-Phase
12	V _{CC(UH)}	High-Side Bias Voltage for U-Phase IC
13	V _{B(U)}	High-Side Bias Voltage for U-Phase IGBT Driving
14	V _{S(U)}	High-SideBias Voltage Ground for U-Phase IGBT Driving
15	IN _(VH)	Signal Input for High-Side V-Phase
16	COM _(H)	High-Side Common Supply Ground
17	V _{CC(VH)}	High-Side Bias Voltage for V-Phase IC
18	V _{B(V)}	High-Side Bias Voltage for V-Phase IGBT Driving
9	V _{S(V)}	High-Side Bias Voltage Ground for V-Phase IGBT Driving
20	IN _(WH)	Signal Input for High-side W-Phase
1	V _{CC(WH)}	High-Side Bias Voltage for W-Phase IC
22	V _{B(W)}	High-Side Bias Voltage for W-Phase IGBT Driving
23	V _{S(W)}	High-Side Bias Voltage Ground for W-Phase IGBT Driving
24	V _{TH}	Thermistor Bias Voltage
25	R _{TH}	Series Resistor for the Use of Thermistor (Temperature Detection)
26	NU	Negative DC-Link Input Terminal for U-Phase
27	N _V	Negative DC-Link Input Terminal for V-Phase
28	NW	Negative DC-Link Input Terminal for W-Phase
29	U	Output for U-Phase
30	V	Output for V-Phase
31	W	Output for W-Phase
32	Р	Positive DC-Link Input



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Absolute Maximum Ratings ($T_J = 25^{\circ}C$, unless otherwise specified.) **Inverter Part**

Item	Symbol	Condition	Rating	Unit
Supply Voltage	V _{DC}	Applied to DC-Link	450	V
Supply Voltage (Surge)	V _{PN(Surge)}	Applied between P and N	500	V
Collector - Emitter Voltage	V _{CES}		600	V
Each IGBT Collector Current	± I _C	T _C = 25°C	20	Α
Each IGBT Collector Current	± I _C	$T_{\rm C} = 100^{\circ}{\rm C}$	14	Α
Each IGBT Collector Current (Peak)	± I _{CP}	T _C = 25°C , Under 1ms Pulse Width	40	Α
Collector Dissipation	P _C	T _C = 25°C per Chip	59	W
Operating Junction Temperature	ТJ	(2nd Note 1)	-20 ~ 125	°C

2nd Notes: 1. It would be recommended that the average junction temperature should be limited to $T_J \le 125^{\circ}C$ (at $T_C \le 100^{\circ}C$) in order to guarantee safe operation.

Control Part

Item	Symbol	Condition	Rating	Unit
Control Supply Voltage	V _{CC}	Applied between $V_{CC(UH)}$, $V_{CC(VH)}$, $V_{CC(WH)}$ - $COM_{(H)}$, $V_{CC(L)}$ - $COM_{(L)}$	20	V
High-Side Control Bias Voltage	V_{BS}	Applied between $V_{B(U)}$ - $V_{S(U)}, V_{B(V)}$ - $V_{S(V)}, V_{B(W)}$ - $V_{S(W)}$	20	V
Input Signal Voltage	V _{IN}	$ \begin{array}{l} \mbox{Applied between IN}_{(UH)}, \mbox{IN}_{(VH)}, \mbox{IN}_{(WH)} \mbox{-} \mbox{COM}_{(H)} \\ \mbox{IN}_{(UL)}, \mbox{IN}_{(VL)}, \mbox{IN}_{(WL)} \mbox{-} \mbox{COM}_{(L)} \end{array} $	-0.3 ~ V _{CC} +0.3	V
Fault Output Supply Voltage	V _{FO}	Applied between V _{FO} - COM _(L)	-0.3 ~ V _{CC} +0.3	V
Fault Output Current	I _{FO}	Sink Current at V _{FO} Pin	5	mA
Current-Sensing Input Voltage	V _{SC}	Applied between C _{SC} - COM _(L)	-0.3 ~ V _{CC} +0.3	V

Total System

Item	Symbol	Condition	Rating	Unit
Self-Protection Supply Voltage Limit (Short-Circuit Protection Capability)	V _{PN(PROT)}	Applied to DC-Link, V _{CC} = V _{BS} = 13.5 ~ 16.5 V T _J = 125°C, Non-Repetitive, < 6 μs	400	V
Module Case Operation Temperature	Т _С	See Figure 2	-20 ~ 100	°C
Storage Temperature	T _{STG}		-20 ~ 125	°C
Isolation Voltage	V _{ISO}	60Hz, Sinusoidal, AC 1 Minute, Connect Pins to Heat Sink Plate	2500	V _{rms}

Thermal Resistance

Item	Symbol	Condition	Min.	Тур.	Max.	Unit
Junction to Case Thermal	R _{th(j-c)Q}	Inverter IGBT Part (per 1/6 module)	-	-	2.10	°C/W
Resistance	R _{th(j-c)F}	Inverter FWDi Part (per 1/6 module)	-	-	3.20	°C/W
Contact Thermal Resistance	R _{th(c-f)}	Ceramic Substrate (per 1 Module) Thermal Grease Applied (2nd Note 3)	-	-	0.06	°C/W

2nd Notes:

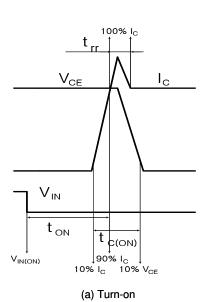
2. For the measurement point of case temperature(T_c), please refer to Figure 2. 3. The thickness of thermal grease should not be more than 100 μ m.

Electrical Characteristics

Inverter Part (T_J = 25°C, unless otherwise specified.)

Item	Symbol	Condition	on	Min.	Тур.	Max.	Unit
Collector - Emitter	V _{CE(SAT)}	V _{CC} = V _{BS} = 15 V V _{IN} = 0 V	$I_{C} = 20 \text{ A}, T_{J} = 25^{\circ}C$	-	-	2.50	V
Saturation Voltage		$V_{IN} = 0 V$	I _C = 20 A, T _J = 125°C	-	-	2.60	V
FWDi Forward Voltage	V _{FM}	V _{IN} = 5 V	$I_{\rm C} = 20 \text{ A}, \text{ T}_{\rm J} = 25^{\circ} \text{C}$	-	-	2.50	V
			$I_{C} = 20 \text{ A}, T_{J} = 125^{\circ}\text{C}$	-	-	2.30	V
Switching Times	t _{ON}	$V_{PN} = 300 \text{ V}, V_{CC} = V_{BS} = 1300 \text{ V}$	5 V	-	0.35	-	μS
	t _{C(ON)}	$I_{C} = 20 \text{ A}, T_{J} = 25^{\circ}\text{C}$		-	0.16	-	μS
	t _{OFF}	V _{IN} = 5 V ↔ 0V, Inductive Lo (High, Low-side)	bad	-	0.75	-	μS
	t _{C(OFF)}	(Thigh, Low-Side)		-	0.23	-	μS
	t _{rr}	(2nd Note 4)		-	0.13	-	μS
Collector - Emitter Leakage Current	I _{CES}	$V_{CE} = V_{CES}, T_J = 25^{\circ}C$		-	-	250	μA

2nd Notes:
 4. t_{ON} and t_{OFF} include the propagation delay time of the internal drive IC. t_{C(OFF)} and t_{C(OFF)} are the switching time of IGBT itself under the given gate driving condition internally. For the detailed information, please see Figure 4.



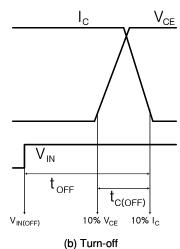


Figure 4. Switching Time Definition

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Item	Symbol	(Condition	Min.	Тур.	Max.	Unit
Quiescent V _{CC} Supply Current	I _{QCCL}	V _{CC} = 15 V IN _(UL, VL, WL) = 5V	V _{CC(L)} - COM _(L)	-	-	26	mA
	IQCCH	V _{CC} = 15 V IN _(UH, VH, WH) = 5V	V _{CC(UH)} , V _{CC(VH)} , V _{CC(WH)} - COM _(H)	-	-	130	μ A
Quiescent V _{BS} Supply Current	I _{QBS}	V _{BS} = 15 V IN _(UH, VH, WH) = 5V	$ \begin{array}{c} V_{B(U)} \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \$	-	-	420	μA
Fault Output Voltage	V _{FOH}		$V_{SC} = 0 \text{ V}, \text{ V}_{FO} \text{ Circuit: } 4.7 \text{ k}\Omega \text{ to } 5 \text{ V} \text{ Pull-up}$		-	-	V
	V _{FOL}	$V_{SC} = 1 V, V_{FO} Circuit$: 4.7 k Ω to 5 V Pull-up	-	-	1.1	V
Short-Circuit Trip Level	V _{SC(ref)}	V _{CC} = 15 V (Note 5)		0.45	0.51	0.56	V
Sensing Voltage of IGBT Current	V _{SEN}	R_{SC} = 50 $\Omega,~R_{SU}$ = R_{SV} = R_{SW} = 0 Ω and I_C = 30 A (See a Figure 6)		0.45	0.51	0.56	V
Supply Circuit Under-	UV _{CCD}	Detection Level		11.5	12.0	12.5	V
Voltage Protection	UV _{CCR}	Reset Level		12.0	12.5	13.0	V
	UV _{BSD}	Detection Level		7.3	9.0	10.8	V
	UV _{BSR}	Reset Level		8.6	10.3	12.0	V
Fault Output Pulse Width	t _{FOD}	C _{FOD} = 33 nF (2nd No	ote 6)	1.4	1.8	2.0	ms
ON Threshold Voltage	V _{IN(ON)}	High-Side	Applied between IN _(UH) ,	-	-	0.8	V
OFF Threshold Voltage	V _{IN(OFF)}		$IN_{(VH)}$, $IN_{(WH)}$ - $COM_{(H)}$	3.0	-	-	V
ON Threshold Voltage	V _{IN(ON)}	Low-Side	Applied between IN _(UL) ,	-	-	0.8	V
OFF Threshold Voltage	V _{IN(OFF)}	1	IN _(VL) , IN _(WL) - COM _(L)	3.0	-	-	V
Resistance of Thermistor	R _{TH}	@ T _{TH} = 25°C (2nd N	ote 7, Figure 5)	-	50	-	kΩ
		@ T _{TH} = 100°C (2nd I	Note 7, Figure 5)	-	3.4	-	kΩ

Electrical Characteristics ($T_J = 25^{\circ}C$, unless otherwise specified.)

2nd Notes:
5. Short-circuit protection is functioning only at the low-sides. It would be recommended that the value of the external sensing resistor (R_{SC}) should be selected around 50 Ω in order to make the SC trip-level of about 30A at the shunt resistors (R_{SU}, R_{SV}, R_{SW}) of 0 Ω. For the detailed information about the relationship between the external sensing resistor (R_{SC}) and the shunt resistors (R_{SU}), R_{SV}, R_{SW}), please see Figure 6.
6. The fault-out pulse width t_{FOD} depends on the capacitance value of C_{FOD} according to the following approximate equation: C_{FOD} = 18.3 x 10⁻⁶ x t_{FOD} [F]
7. T_{TH} is the temperature of thermistor itself. To know case temperature (T_C), please make the experiment considering your application.

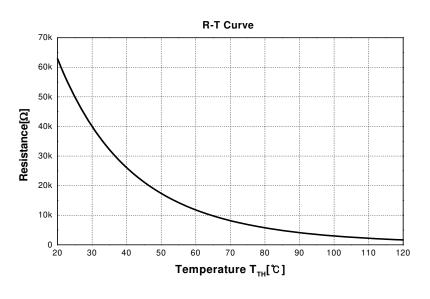


Figure 5. R-T Curve of The Built-in Thermistor

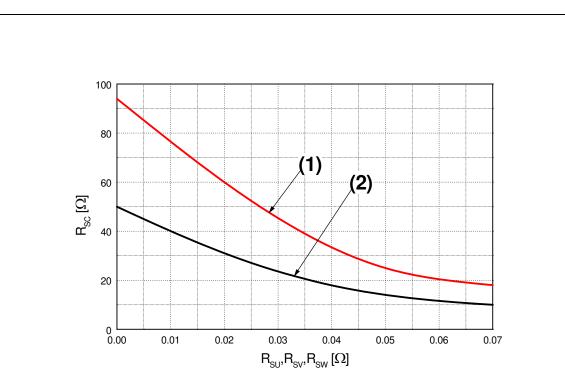


Figure 6. R_{SC} Variation by Change of Shunt Resistors (R_{SU}, R_{SV}, R_{SW}) for Short-Circuit Protection(1) @ Current Trip Level \Rightarrow 20 A(2) @ Current Trip Level \Rightarrow 30 A

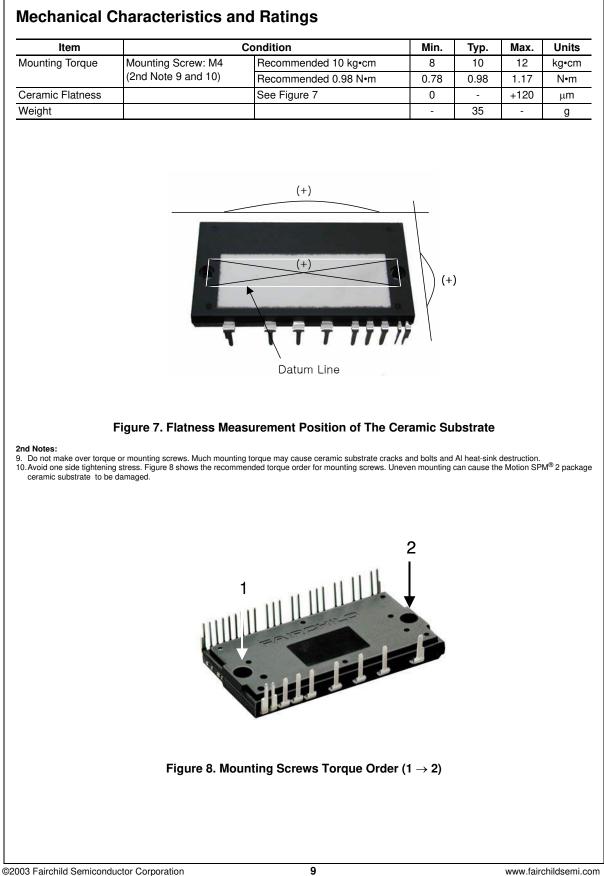
ricoonnichaea operating conditions	Recommended	Operating	Conditions
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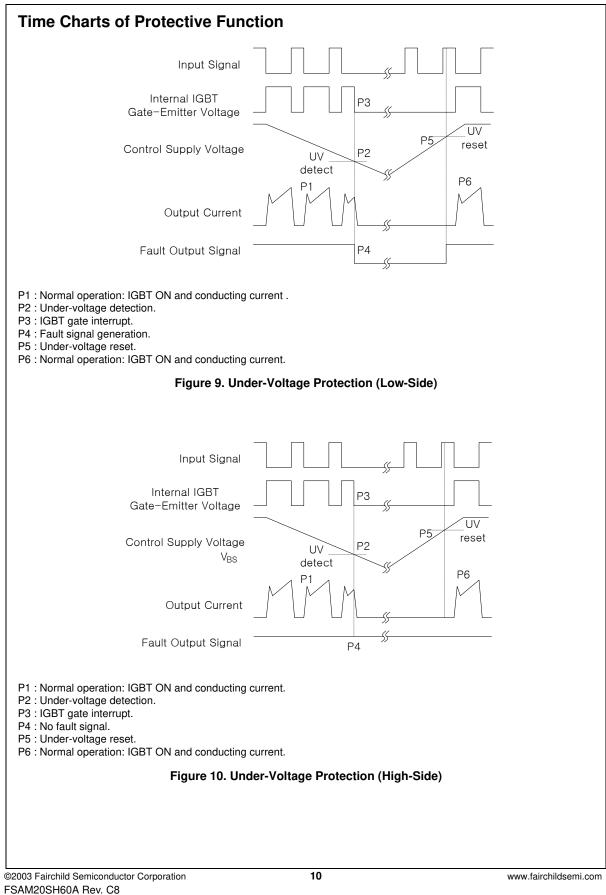
Item	Symbol	Condition	Min.	Тур.	Max.	Unit
Supply Voltage	V _{PN}	Applied between P - N _U , N _V , N _W	-	300	400	V
Control Supply Voltage	V _{CC}	Applied between $V_{CC(UH)}$, $V_{CC(VH)}$, $V_{CC(WH)}$ - $COM_{(H)}$, $V_{CC(L)}$ - $COM_{(L)}$	13.5	15.0	16.5	V
High-side Bias Voltage	V _{BS}	Applied between $V_{B(U)}$ - $V_{S(U)}$, $V_{B(V)}$ - $V_{S(V)}$, $V_{B(W)}$ - $V_{S(W)}$,	13.0	15.0	18.5	V
Blanking Time for Preventing Arm-short	t _{dead}	For Each Input Signal	3.0	-	-	μS
PWM Input Signal	f _{PWM}	$T_C \le 100^{\circ}C, T_J \le 125^{\circ}C$	-	15	-	kHz
Minimum Input Pulse Width	PW _{IN(OFF)}	$\begin{array}{l} 200 \leq V_{PN} \leq 400 \text{V}, 13.5 \leq V_{CC} \leq 16.5 \text{V}, \\ 13.0 \leq V_{BS} \leq 18.5 \text{V}, 0 \leq \text{I}_C \leq 40 \text{A}, \\ -20 \leq \text{T}_J \leq 125 ^{\circ} \text{C} \\ \text{V}_{IN} = 5 \text{V} \leftrightarrow 0 \text{V}, \text{Inductive Load} (\text{2nd Note 8}) \end{array}$	3	-	-	μS
Input ON Threshold Voltage	V _{IN(ON)}	$\begin{array}{l} \text{Applied between IN}_{(\text{UH})}, \text{IN}_{(\text{VH})}, \text{IN}_{(\text{WH})} \text{ - } \\ \text{COM}_{(\text{H})}, \text{IN}_{(\text{UL})}, \text{IN}_{(\text{VL})}, \text{IN}_{(\text{WL})} \text{ - } \text{COM}_{(\text{L})} \end{array}$		0 ~ 0.65	5	V
Input OFF Threshold Voltage	V _{IN(OFF)}	Applied between IN _(UH) , IN _(VH) , IN _(WH) - COM _(H) , IN _(UL) , IN _(VL) , IN _(WL) - COM _(L)		4 ~ 5.5		V

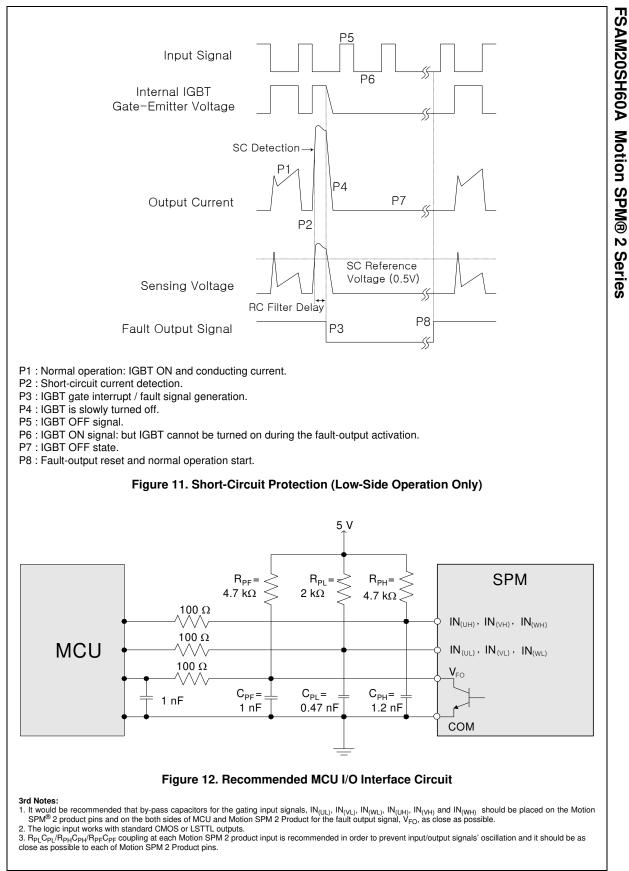
 $\begin{array}{l} \textbf{2nd Notes:} \\ \textbf{8. Motion SPM}^{\textcircled{O}} \ \textbf{2 product might not make response if the PW_{IN(OFF)} is less than the recommended minimum value. \end{array}$

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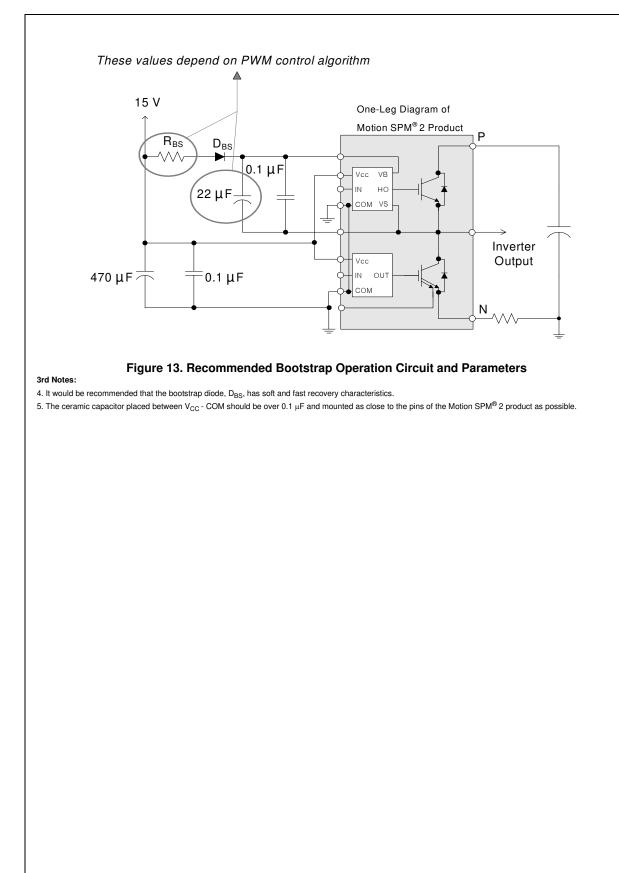
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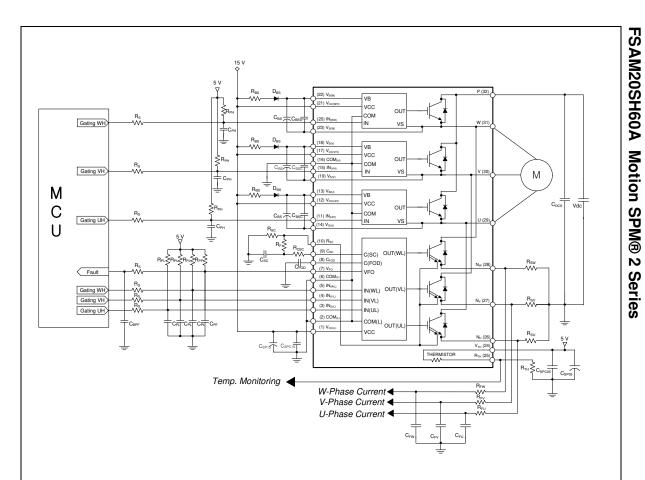
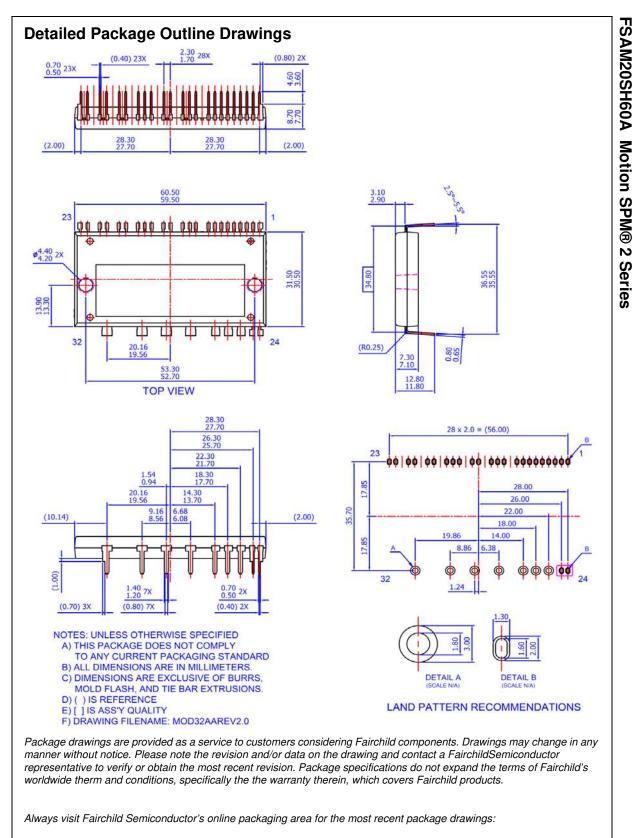


Figure 14. Application Circuit

4th Notes:

- 1. Rp_CPL/RpHCPH /RpFCPF coupling at each Motion SPM[®] 2 product input is recommended in order to prevent input signals' oscillation and it should be as close as possible to each Motion SPM 2 product input pin.
- 2. By virtue of integrating an application specific type HVIC inside the Motion SPM 2 product, direct coupling to MCU terminals without any optocoupler or transformer isolation is possible.
- 3. V_{FO} output is open-collector type. This signal line should be pulled up to the positive side of the 5 V power supply with approximately 4.7 kΩ resistance. Please refer to Figure 12.
- 4. Spris of around seven times larger than bootstrap capacitor C_{BS} is recommended.
 5. V_{FO} output pulse width should be determined by connecting an external capacitor(C_{FOD}) between C_{FOD}(pin 8) and COM_(L)(pin 2). (Example : if C_{FOD} = 33 nF, then
- 5. V_{FO} output puise what should be determined by connecting an external capacitor(C_{FOD}) between $C_{FOD}(pin 8)$ and $COM_{(L)}(pin 2)$. (Example : If $C_{FOD} = 33$ nF, then $t_{FO} = 1.8$ ms (typ.)) Please refer to the 2nd note 6 for calculation method. 6. Each input signal line should be pulled up to the 5 V power supply with approximately 4.7 k Ω (at high side input) or 2 k Ω (at low side input) resistance (other RC coupling circuits at each input may be needed depending on the PWM control scheme used and on the wiring impedance of the system's printed circuit board). Approximately a 0.22 ~ 2 nF by pass capacitor should be used across each power supply connection terminals.

- Approximately a 0.22 ~ 2 in by pass capacitor should be used across each power supply connection terminals. 7. To prevent errors of the protection function, the wiring around R_{SC} , R_F and C_{SC} should be as short as possible. 8. In the short-circuit protection circuit, please select the $R_F C_{SC}$ time constant in the range 3 ~ 4 µs. 9. Each capacitor should be mounted as close to the pins of the Motion SPM 2 product as possible. 10. To prevent surge destruction, the wiring between the smoothing capacitor and the P & N pins should be as short as possible. The use of a high frequency non-independent surge destruction of a log of the DON big terms and the P & N pins should be as short as possible. The use of a high frequency non-independent surger destruction of the DON big terms and the P & N pins should be as short as possible. The use of a high frequency non-
- inductive capacitor of around 0.1 ~ 0.22 µF between the P&N pins is recommended. 11. Relays are used at almost every systems of electrical equipments of home appliances. In these cases, there is hould be sufficient distance between the MCU and the relays. It is recommended that the distance be 5 cm at least.



http://www.fairchildsemi.com/dwg/MO/MOD32AA.pdf

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